FREE

Vishay Semiconductors

www.vishay.com

Hyperfast Rectifier, 15 A FRED Pt[®] G5



LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS					
I _{F(AV)}	15 A				
V _R	1200 V				
V _F at I _F at 125 °C	1.7 V				
t _{rr}	37 ns				
T _J max.	175 °C				
Package	2L TO-220AC				
Circuit configuration	Single				

FEATURES

- Hyperfast and optimized Q_{rr}
- Best in class forward voltage drop and switching RoHS
 losses trade off
 HALOGEN
- Optimized for high speed operation
- 175 °C maximum operating junction temperature
- Polyimide passivation
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

Featuring a unique combination of low conduction and switching losses, this rectifier is the right choice for high frequency converters, both soft switched / resonant.

Specifically designed to improve efficiency of PFC and output rectification stages of EV / HEV battery charging stations, booster stage of solar inverters and UPS applications, these devices are perfectly matched to operate with MOSFETs or high speed IGBTs.

MECHANICAL DATA

Case: 2L TO-220AC

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

Polarity: as per marking device details

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Repetitive peak reverse voltage	V _{RRM}		1200	V			
Average rectified forward current	I _{F(AV)}	T _C = 110 °C, D = 0.50	15				
Repetitive peak forward current	I _{FRM}	T _C = 110 °C, D = 0.50, f = 20 kHz	30	А			
Non-repetitive peak surge current	I _{FSM}	T_{C} = 45 °C, t_{p} = 10 ms, sine wave	125				
Operating junction and storage temperature	T _J , T _{Stg}		-55 to +175	°C			

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	1200	-	-			
	V _F	I _F = 15 A	-	1.9	2.5	V		
Forward voltage		I _F = 15 A, T _J = 125 °C	-	1.7	-			
	I _R	$V_{R} = V_{R}$ rated	-	-	50			
Reverse leakage current		$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	-	500	μA		
Junction capacitance	CT	V _R = 200 V	-	10	-	pF		
Series inductance	L _S	Measured to lead 5 mm from package body	-	8	-	nH		

 Revision: 30-Jul-2020
 1
 Document Number: 96581

 For technical questions within your region: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com
 DiodesEurope@vishay.com

 THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000



www.vishay.com

Vishay Semiconductors

DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
		I _F = 1.0 A, dI _F /dt =	100 A/ μ s, V _R = 30 V	-	37	50			
Reverse recovery time	t _{rr}	T _J = 25 °C		-	95	-	ns		
		T _J = 125 °C		-	146	-			
Peak recovery current		T _J = 25 °C	l _F = 10 A dl _F /dt = 600 A/µs	-	14	-	A		
Feak recovery current	IRRM	T _J = 125 °C	$V_{\rm R} = 400 \text{ V}$	-	19	-			
Powerso recovery charge	0	T _J = 25 °C		-	545	-	nC		
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	1200	-			
Reverse recovery time	+	T _J = 25 °C		-	75.5	-	20		
Reverse recovery time	t _{rr}	T _J = 125 °C		-	100	-	ns		
Deels receiver a current		T _J = 25 °C	$I_{\rm F} = 15 {\rm A}$	-	23	-	А		
Peak recovery current	IRRM	T _J = 125 °C	dI _F /dt = 1000 A/µs V _R = 800 V	-	35	-			
	0	T _J = 25 °C		-	935	-			
Reverse recovery charge	Q _{rr}	T _J = 125 °C	1	-	1985	-	nC		

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Thermal resistance, junction-to-case	R _{thJC}		-	-	1.7	°C/W		
Weight			-	2.0	-	g		
Weight			-	0.07	-	oz.		
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)		
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C		
Marking device		Case style 2L TO-220AC	E5TH1512					

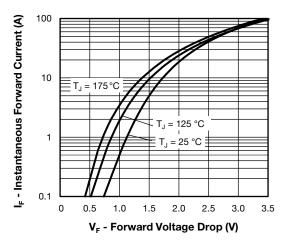


Fig. 1 - Forward Voltage Drop Characteristics

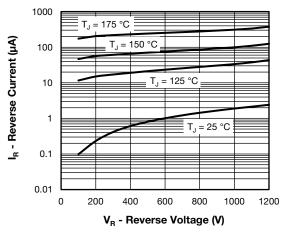


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



VS-E5TH1512-M3

Vishay Semiconductors

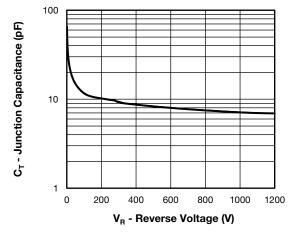


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

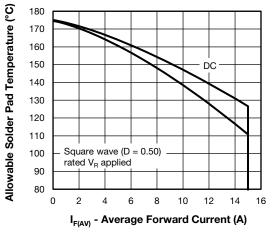


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

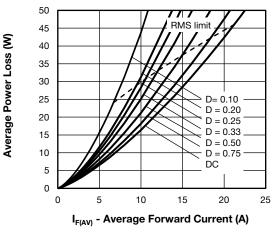


Fig. 5 - Forward Power Loss Characteristics

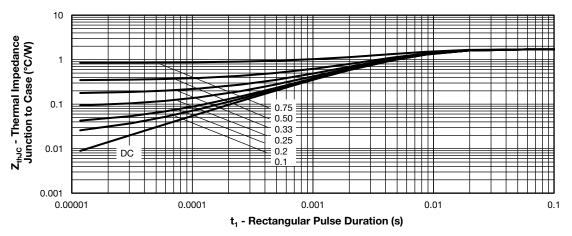
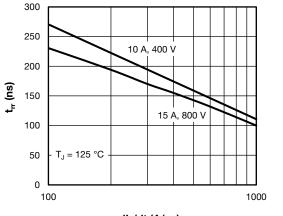


Fig. 6 - Transient Thermal Impedance, Junction to Case

Revision: 30-Jul-2020



Vishay Semiconductors

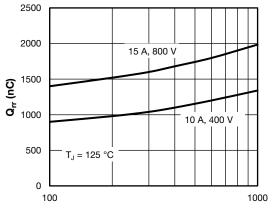


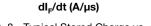
www.vishay.com

SHAY

dl_F/dt (A/µs)

Fig. 7 - Typical Reverse Recovery Time vs. dI_F/dt







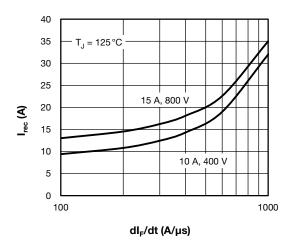


Fig. 9 - Typical Stored Charge vs. dl_F/dt



VISHAY. www.vishay.com

Vishay Semiconductors

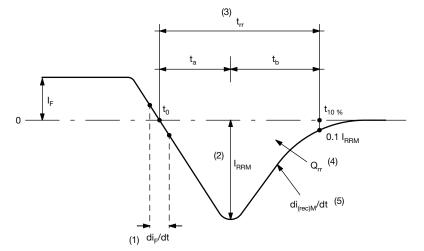


Fig. 10 - Reverse Recovery Waveform and Definitions

Notes

- $^{(1)}$ di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- $^{(3)}$ t_{rr} reverse recovery time measured from t₀, crossing point of negative going I_F, to point t_{10%}, 0.1 I_{RRM}
- $^{(4)}~~\text{Q}_{rr}$ area under curve defined by t_0 and $t_{10}~\%$

$$Q_{rr} = \int_{t_0}^{t_{10\%}} I(t)dt$$

 $^{(5)}$ di_{(rec)}M/dt - peak rate of change of current during t_b portion of t_{rr}

ORDERING INFORMATION TABLE

Device code	VS-	E	5	т	н	15	12	-МЗ
	1	2	3	4	5	6	7	8
	1 -	- Visł	nay Sem	niconduo	ctors pr	oduct		
	2 -	• E=	single o	diode				
	3 -	- 5 =	FRED g	jeneratio	on 5			
	4 -	· Pac	kage:					
			2L TO-2					
	5 -	• H=	hyperta	ast recov	very			
	6 -	- Cur	rent rati	ng (15 =	= 15 A)			
	7 -	- Volt	age rati	ing (12 =	= 1200 \	/)		
	8 -	- Env	ironmer	ntal digit				
		-M3	3 = halog	gen-free	e, RoHS	-compli	ant, an	d termin

ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-E5TH1512-M3	50	1000	Antistatic plastic tube			

LINKS TO RELATED DOCUMENTS		
Dimensions	<u>wwv</u>	w.vishay.com/doc?96154
Part marking information	<u>wwv</u>	w.vishay.com/doc?95391
Revision: 30-Jul-2020	5	Document Number: 96581
For technical questions within your region	n: <u>DiodesAmericas@vishay.com</u> , <u>DiodesAsia@v</u>	ishay.com, DiodesEurope@vishay.com

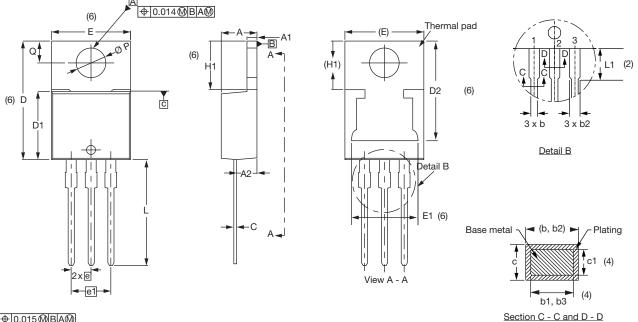
THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000



Vishay Semiconductors

3L TO-220AB

DIMENSIONS in millimeters and inches



⊕0.015@BA@





SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STINDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.50	2.92	0.098	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.35	0.585	0.604	3
D1	8.38	9.02	0.330	0.355	

_		
Conforms to JEDEC [®]	outline	TO-220AB

SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STINDOL	MIN.	MAX.	MIN.	MAX.	NOTES
D2	11.68	13.30	0.460	0.524	6, 7
Ш	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØР	3.54	3.91	0.139	0.154	
Q	2.60	3.00	0.102	0.118	

Notes

⁽²⁾ Lead dimension and finish uncontrolled in L1

- ⁽⁴⁾ Dimension b1, b3, and c1 apply to base metal only
- (5) Controlling dimensions: inches
- ⁽⁶⁾ Thermal pad contour optional within dimensions E, H1, D2, and E1
- ⁽⁷⁾ Outline conforms to JEDEC[®] TO-220, except D2

Revision: 13-Jun-2019

 $^{^{(1)}\,}$ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽³⁾ Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.